

# TransEON

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Edmonton, AB, Canada

## TransEON Announces the GaN MOSFET

TransEON Inc., a Canadian stealth-mode startup, has developed a new MOSFET-based GaN-on-SiC foundry process that enables fabrication of cutting-edge transistors and MMICs with significant benefits over existing GaN HEMT technology. Key advantages include up to 4x higher operating voltage and RF power density at frequencies ranging from HF up to W-band.

The process includes standard MMIC features to provide turnkey compatibility with existing GaN processes, including through-substrate vias, integrated passives, and Au-plated microstrip on thinned SiC. Other advantages of this offering include full process customization, high-touch design and NRE services, ITAR and ITAR-free compatibility, as well as industry-leading cycle times and multi-project wafer access.

The GaN MOSFET process, the first commercial platform of its kind, will be formally unveiled at IMS2024 in Washington, D.C. from June 18<sup>th</sup> through June 20<sup>th</sup>. TransEON will host an official launch event at the Marriott Marquis Independence Salon D at 1 PM on Tuesday June 18<sup>th</sup>, directly accessible from the Walter E. Washington Convention Center Concourse (Level C). Pre-registration is required and [can be completed online](#). Staff will also be present at Booth 2343 on the trade show, and one-on-one meetings [can be requested in advance](#).

To learn more about TransEON and the GaN MOSFET process, please [subscribe for email updates](#) or reach out directly to [info@transeon.ca](mailto:info@transeon.ca).

